

2N7000

Preferred Device

Small Signal MOSFET 200 mAmps, 60 Volts N-Channel TO-92

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V_{DGR}	60	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
- Continuous	V_{GSM}	± 40	Vpk
- Non-repetitive ($t_p \leq 50 \mu\text{s}$)			
Drain Current	I_D	200	mAdc
- Continuous	I_{DM}	500	
- Pulsed			
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.8	mW mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to $+150$	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	T_L	300	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



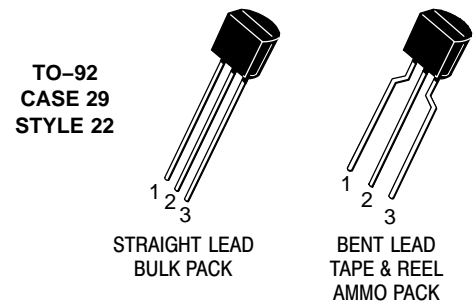
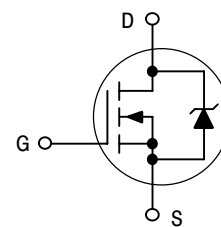
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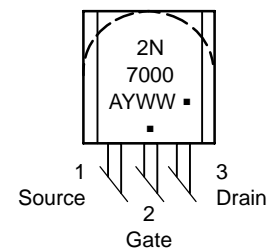
**200 mAmps
60 Volts**

$R_{DS(on)} = 5 \Omega$

N-Channel



MARKING DIAGRAM AND PIN ASSIGNMENT



- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage	$(V_{GS} = 0, I_D = 10 \mu\text{Adc})$	$V_{(BR)DSS}$	60	-	Vdc
Zero Gate Voltage Drain Current	$(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0)$ $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0, T_J = 125^\circ\text{C})$	I_{DSS}	-	1.0	μAdc mAdc
Gate-Body Leakage Current, Forward	$(V_{GSF} = 15 \text{ Vdc}, V_{DS} = 0)$	I_{GSSF}	-	-10	nAdc

ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage	$(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$	$V_{GS(th)}$	0.8	3.0	Vdc
Static Drain-Source On-Resistance	$(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc})$	$r_{DS(on)}$	-	5.0	Ω
Drain-Source On-Voltage	$(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc})$	$V_{DS(on)}$	-	2.5	Vdc
On-State Drain Current	$(V_{GS} = 4.5 \text{ Vdc}, V_{DS} = 10 \text{ Vdc})$	$I_{d(on)}$	75	-	mAdc
Forward Transconductance	$(V_{DS} = 10 \text{ Vdc}, I_D = 200 \text{ mAdc})$	g_{fs}	100	-	μmhos

DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = 25 \text{ V}, V_{GS} = 0,$ $f = 1.0 \text{ MHz})$	C_{iss}	-	60	pF
Output Capacitance		C_{oss}	-	25	
Reverse Transfer Capacitance		C_{rss}	-	5.0	

SWITCHING CHARACTERISTICS (Note 1)

Turn-On Delay Time	$(V_{DD} = 15 \text{ V}, I_D = 500 \text{ mA},$ $R_G = 25 \Omega, R_L = 30 \Omega, V_{gen} = 10 \text{ V})$	t_{on}	-	10	ns
Turn-Off Delay Time		t_{off}	-	10	

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

Device	Package	Shipping [†]
2N7000	TO-92	1000 Units / Bulk
2N7000G	TO-92 (Pb-Free)	1000 Units / Bulk
2N7000RLRA	TO-92	2000 Tape & Reel
2N7000RLRAG	TO-92 (Pb-Free)	2000 Tape & Reel
2N7000RLRM	TO-92	2000 Tape & Ammo Box
2N7000RLRMG	TO-92 (Pb-Free)	2000 Tape & Ammo Box
2N7000RLRP	TO-92	2000 Tape & Ammo Box
2N7000RLRPG	TO-92 (Pb-Free)	2000 Tape & Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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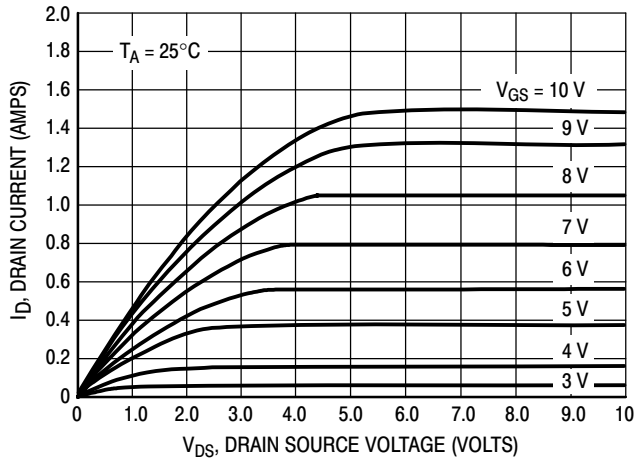


Figure 1. Ohmic Region

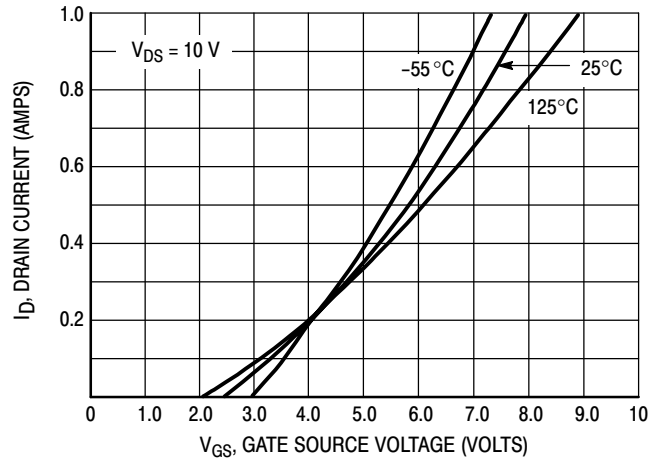


Figure 2. Transfer Characteristics

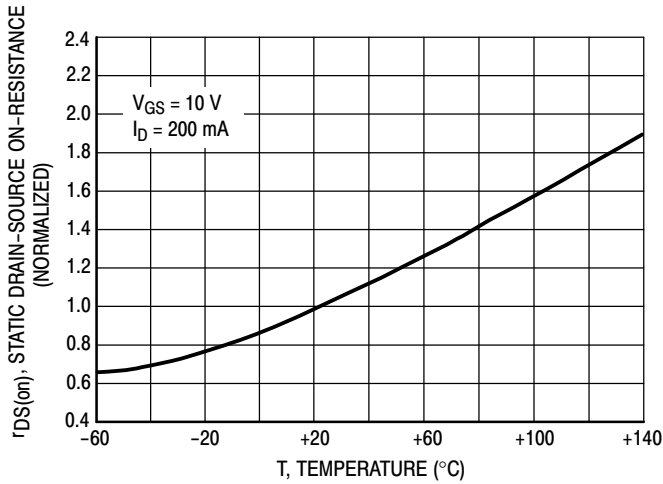


Figure 3. Temperature versus Static Drain-Source On-Resistance

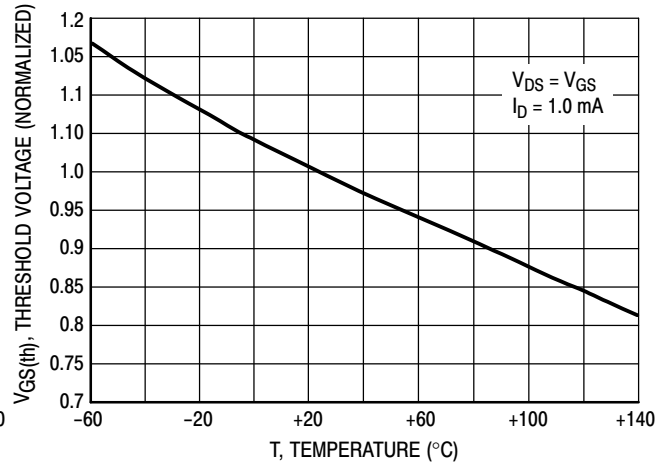
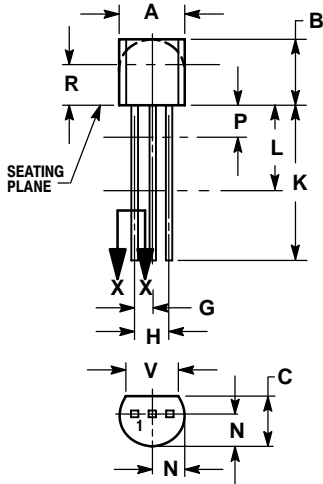


Figure 4. Temperature versus Gate Threshold Voltage

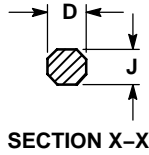
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PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-11
ISSUE AM



STRAIGHT LEAD
BULK PACK

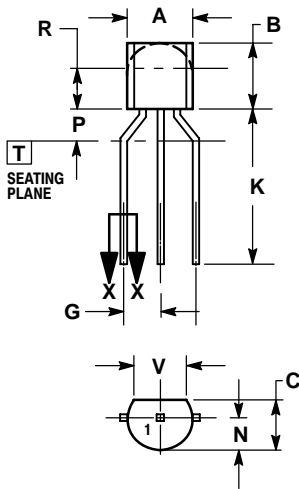


SECTION X-X

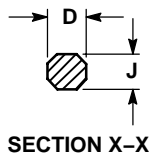
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



SECTION X-X

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 22:

1. SOURCE
2. GATE
3. DRAIN

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